

1. General description

Planar passivated high commutation three quadrant triac in a TO92 plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This series triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High blocking voltage capability
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- General purpose motor control circuits
- Home appliances
- Solenoid drivers

4. Quick reference data

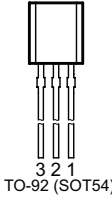
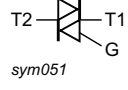
Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute maximum rating				
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; Fig. 1 ; Fig. 2 ; Fig. 3	3	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $t_p = 16.7$ ms; $T_{j(\text{init})} = 25$ °C	30	A
		full sine wave; $t_p = 20$ ms; $T_{j(\text{init})} = 25$ °C Fig. 4 ; Fig. 5	27	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	-	30	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	-	30	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	-	30	mA
V_T	on-state voltage	$I_T = 5\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10	-	1.4	1.7	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_j = 125\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	2000	-	-	V/ μs
		$V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1500	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}; T_j = 150\text{ }^\circ\text{C}; I_{T(RMS)} = 3\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ (snubberless condition); gate open circuit	5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 <p>TO-92 (SOT54)</p>	 <p>sym051</p>
2	G	gate		
3	T1	main terminal 1		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA203-800CT	TO92	BTA203-800CTEP	Bulk	1000	SOT54	14-Nov-2013
BTA203-800CT	TO92	BTA203-800CTQP	Reel	2000	SOT54 wide pitch	14-Nov-2013
BTA203-800CT/L01	TO92	BTA203-800CT/L01EP	Bulk	500	SOT54/L01	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA203-800CT	203-8C

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; Fig. 1 ; Fig. 2 ; Fig. 3	3	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $t_p = 16.7$ ms; $T_{j(init)} = 25$ °C	30	A
		full sine wave; $t_p = 20$ ms; $T_{j(init)} = 25$ °C; Fig. 4 ; Fig. 5	27	A
I^2t	I^2t for fusing	$t_p = 10$ ms; sine wave	3.7	A ² s
di_T/dt	rate of rise of on-state current	$I_G = 60$ mA	100	A/ μ s
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.3	W
T_{stg}	storage temperature		-40 to 150	°C
T_j	junction temperature		150	°C

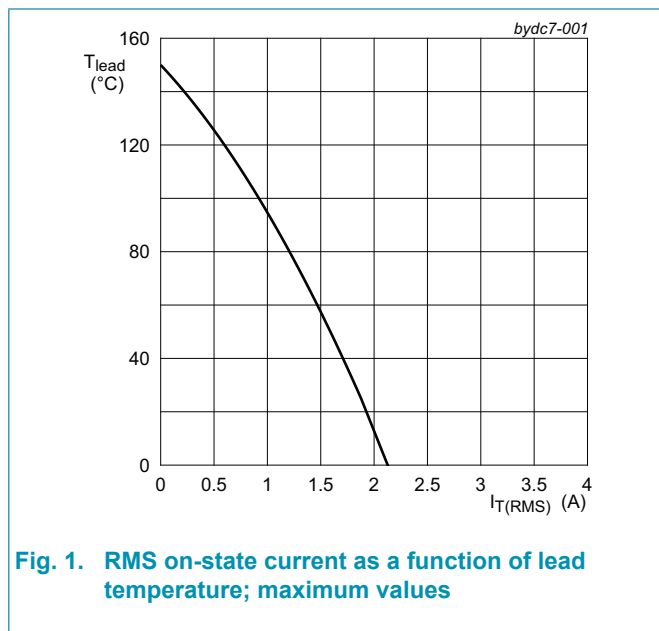


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

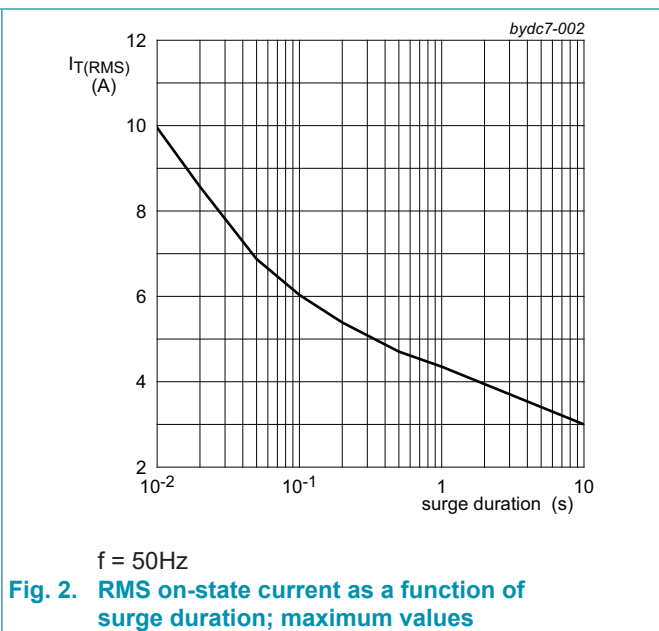
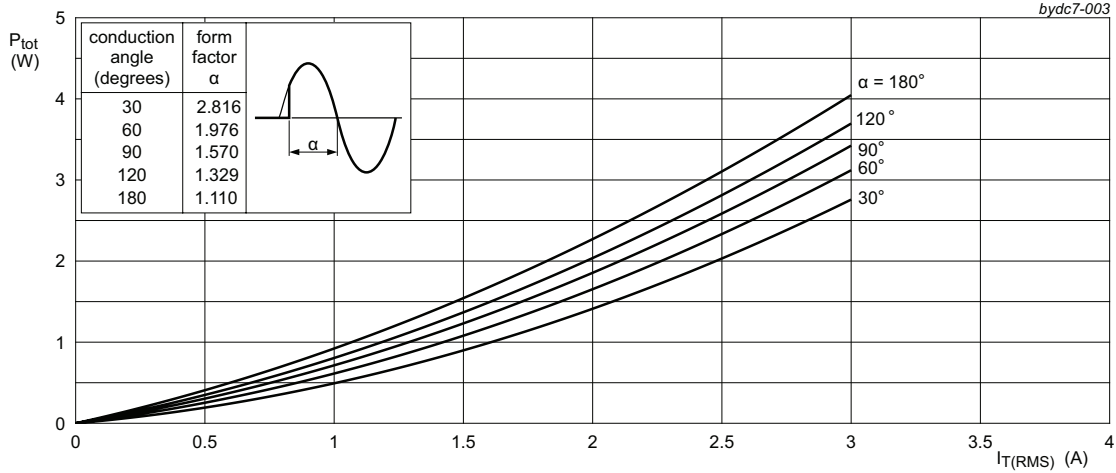
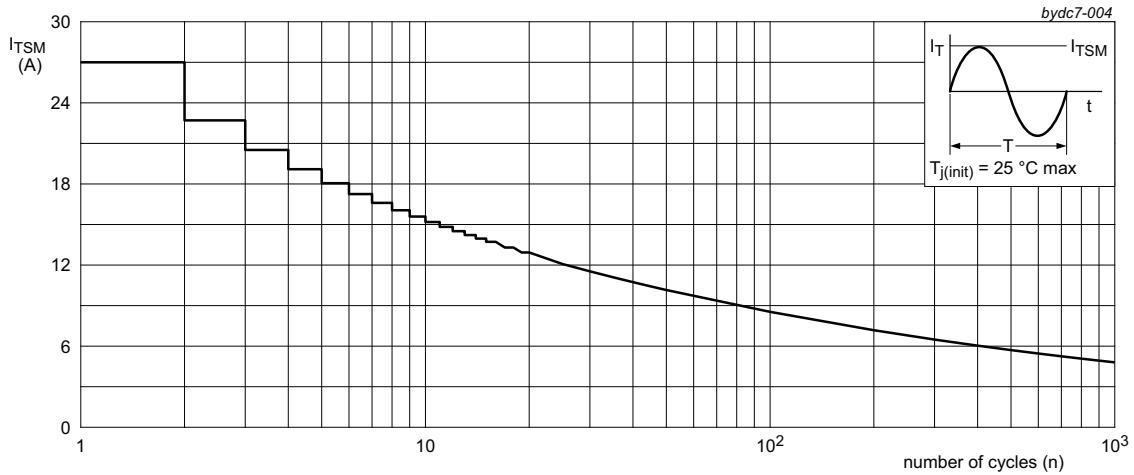


Fig. 2. RMS on-state current as a function of surge duration; maximum values
f = 50Hz



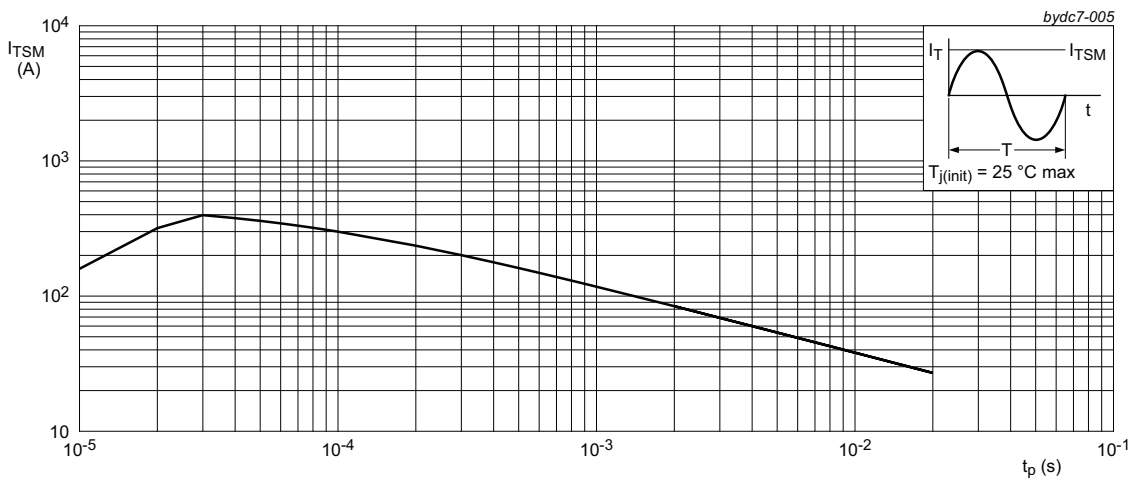
α = conduction angle
 a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$f = 50 \text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20 \text{ ms}$;
 (1) di_T/dt limit

Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

9. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	150	-	K/W

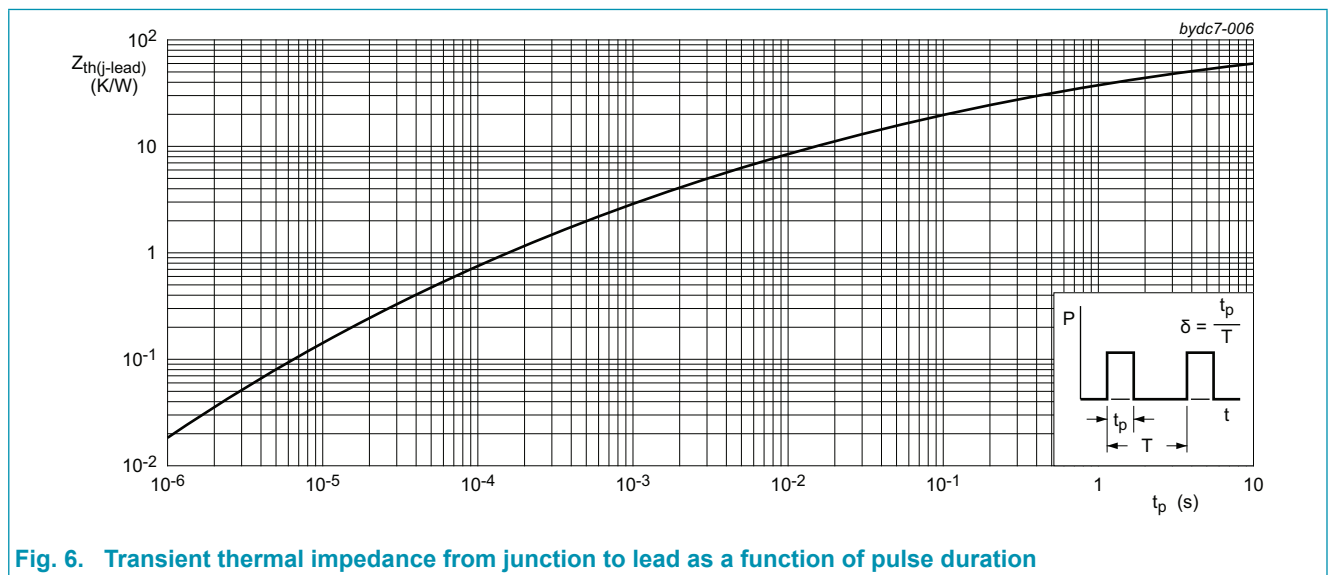
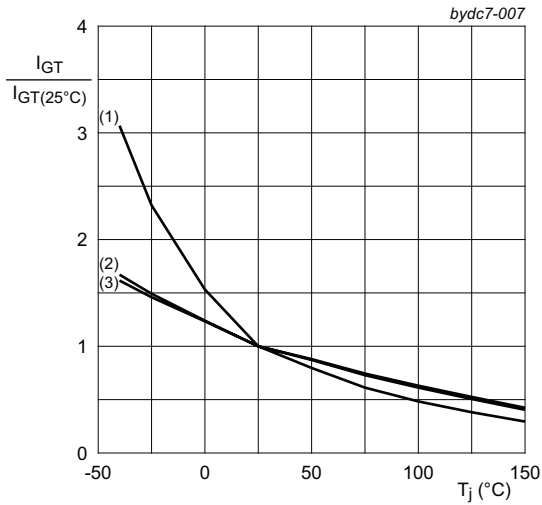


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 7	-	-	30	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 7	-	-	30	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 7	-	-	30	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 8	-	-	30	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 8	-	-	60	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 8	-	-	30	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 9	-	-	30	mA
V_T	on-state voltage	$I_T = 5\text{ A}$; $T_J = 25\text{ °C}$; Fig. 10	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$; Fig. 11	-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 150\text{ °C}$	0.25	0.45	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_J = 25\text{ °C}$	-	-	10	μA
		$V_D = 800\text{ V}$; $T_J = 150\text{ °C}$	-	-	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	2000	-	-	V/ μs
		$V_{DM} = 536\text{ V}$; $T_J = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1500	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 3\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

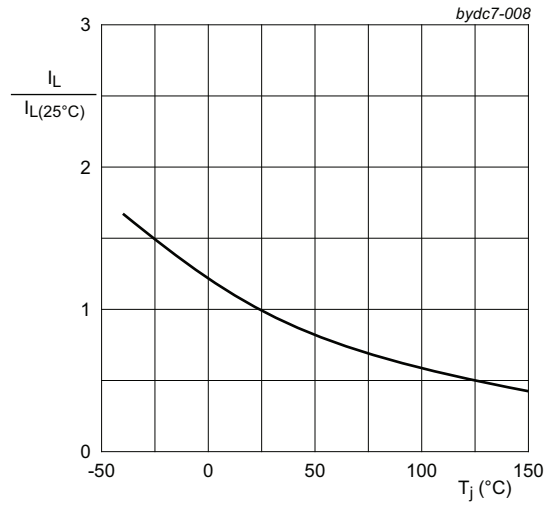


Fig. 8. Normalized latching current as a function of junction temperature

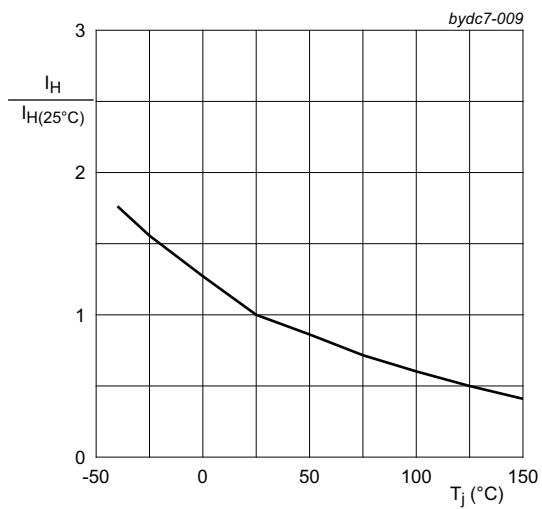
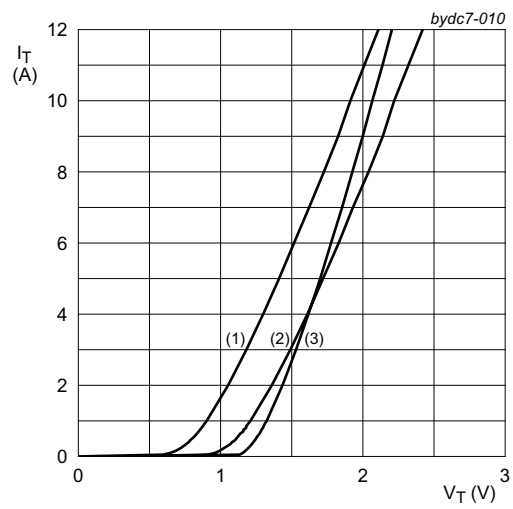


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 0.787 \text{ V}; R_s = 0.2133 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

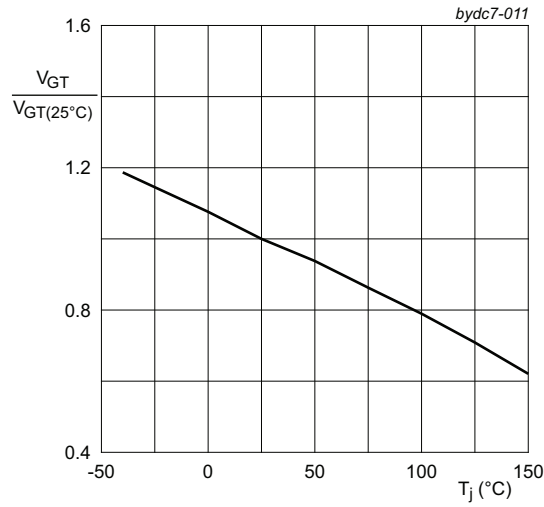
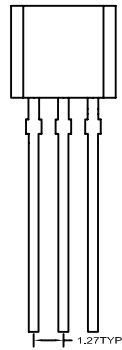


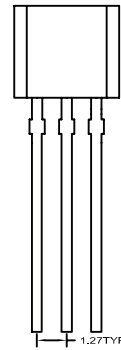
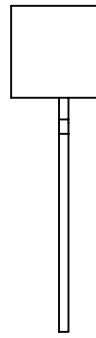
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

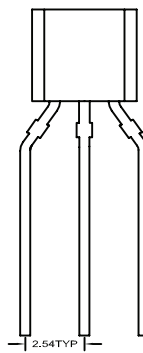
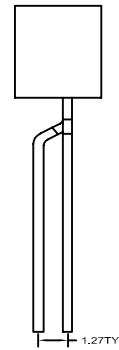
SOT54 PACKAGE OUTLINE



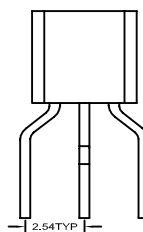
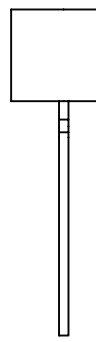
SOT54
Bulk Pack - 412



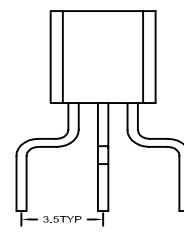
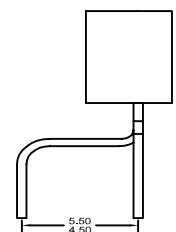
SOT54 LEADS ON CIRCLE
Bulk Pack - 112



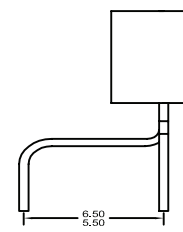
SOT54 WIDE PITCH
Tape/ Reel Pack - 116
Ammo Pack - 126



SOT54 LEAD BEND L01
Bulk Pack - 412



SOT54 LEAD BEND L02
Bulk Pack - 412



Remark: Detailed dimensions refer to POD drawing.

12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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